

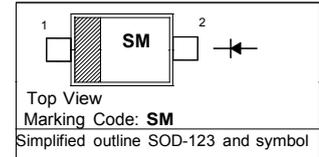
Surface Mount Schottky Barrier Diodes

Features

- Low forward voltage
- Low reverse capacitance

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

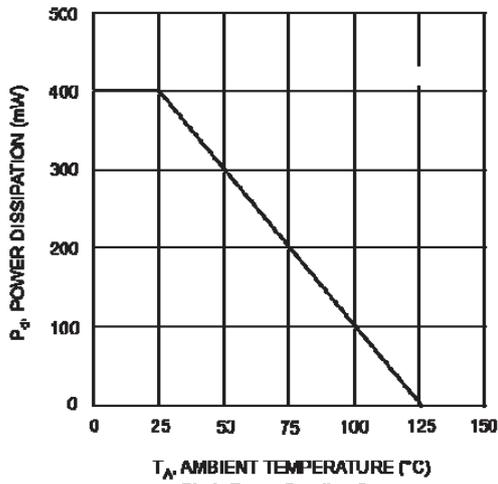


Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

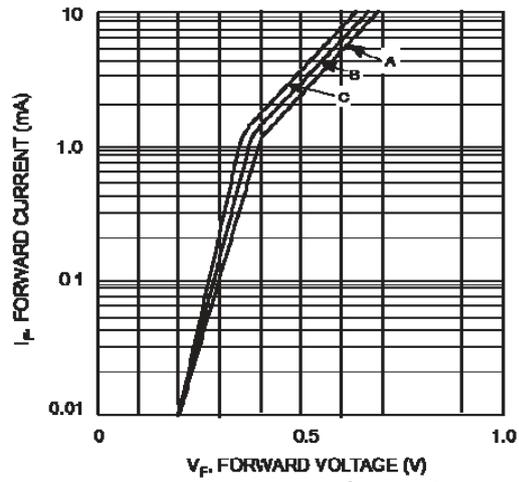
Parameter	Symbol	Value	Unit		
Peak Repetitive Reverse Voltage	V_{RRM}	SD101AW SD101BW SD101CW	60 50 40	V	
Reverse Voltage		V_R	SD101AW SD101BW SD101CW	60 50 40	V
Forward Continuous Current			I_{FM}	15	mA
Power Dissipation	P_d		400	mW	
Non-Repetitive Peak Forward Surge Current	I_{FSM}	at $t = 1\text{ s}$ at $t = 10\text{ }\mu\text{s}$	50 2	mA A	
Operating and Storage Temperature Range		T_j, T_{stg}	- 65 to + 125	$^\circ\text{C}$	

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

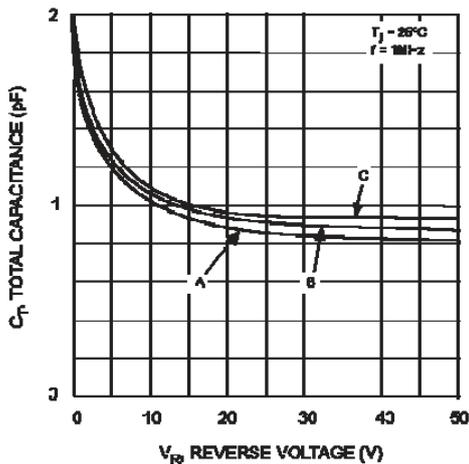
Parameter	Symbol	Min.	Max.	Unit		
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	$V_{(BR)R}$	SD101AW SD101BW SD101CW	60 50 40	- - - V		
Forward Voltage at $I_F = 1\text{ mA}$		V_F	SD101AW SD101BW SD101CW	- - - 0.41 0.4 0.39	V	
at $I_F = 15\text{ mA}$			SD101AW SD101BW SD101CW	- - - 1 0.95 0.9		
Reverse Current at $V_R = 50\text{ V}$ at $V_R = 40\text{ V}$ at $V_R = 30\text{ V}$	I_R		SD101AW SD101BW SD101CW	- - - 200 200 200	nA	
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$			C_T	SD101AW SD101BW SD101CW	- - - 2 2.1 2.2	pF
Reverse Recovery Time at $I_F = I_R = 5\text{ mA}$, $I_{rr} = 0.1X I_R$, $R_L = 100\text{ }\Omega$				t_{rr}	-	1



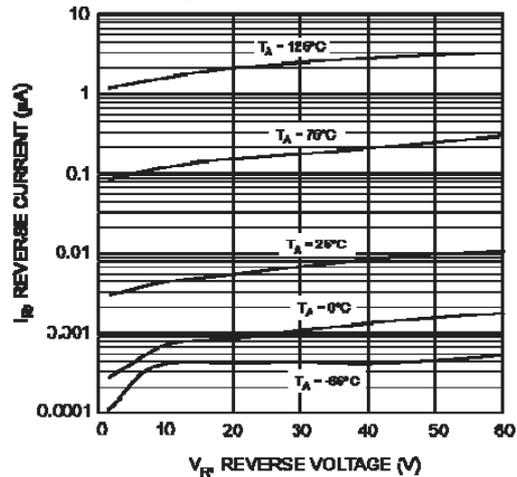
T_A , AMBIENT TEMPERATURE (°C)
Fig. 1 Power Derating Curve



V_F , FORWARD VOLTAGE (V)
Fig. 2 Typical Forward Characteristic



C_T , TOTAL CAPACITANCE (pF)
 V_{R} , REVERSE VOLTAGE (V)
Fig. 3 Typical Total Capacitance vs Reverse Voltage



I_R , REVERSE CURRENT (µA)
 V_{R} , REVERSE VOLTAGE (V)
Fig. 4 Typical Reverse Characteristics